性能特点：

- 频率范围：DC-50GHz
- 衰减范围：0/1/2/3/4/5/6/7/8/9/10dB
- 插损波动：0.4dB
- 输入/输出电压驻波比：1.4/1.4
- 芯片尺寸：0.60mm×0.60mm×0.1mm

产品简介：

HH-AT50 是一款性能优良的 GaAs MMIC 固定衰减器。芯片覆盖 DC-50GHz 频带范围，衰减范围可选，插损波动小于 0.4dB，输入输出电压驻波比小于 1.4。

电参数：（T_A=25℃)

指标		最小值	典型值	最大值	单位
频率范围		DC-50			GHz
衰减量	0dB	0	0	0.5	dB
	1dB	0.8	1	1.3	dB
	2dB	2	2	2.4	dB
	3dB	3	3	3.4	dB
	4dB	4	4	4.4	dB
	5dB	5	5	5.4	dB
	6dB	6	6	6.4	dB
	7dB	7	7	7.4	dB
	8dB	8	8	8.4	dB
	9dB	9	9	9.4	dB
	10dB	10	10	10.3	dB
输入驻波比		-	1.2	1.4	-
输出驻波比		-	1.2	1.4	-

使用限制参数：(超过以上任何一项最大限额都有可能造成永久损坏。)

最大输入功率	27 dBm
存储温度	-65℃-150℃
使用温度	-55℃-125℃

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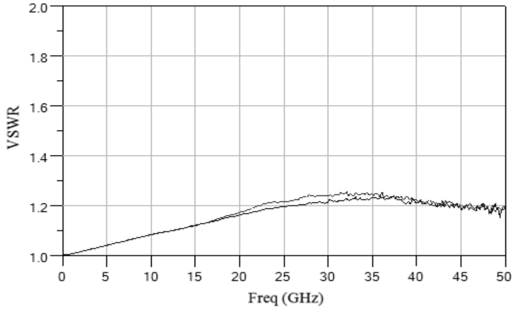
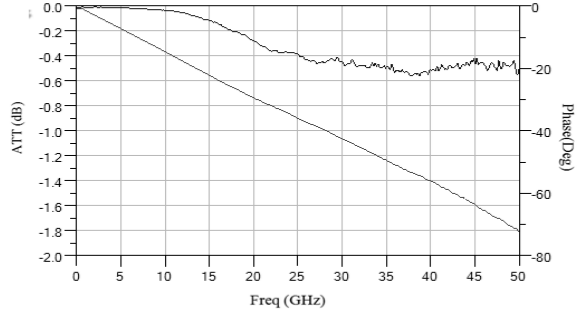
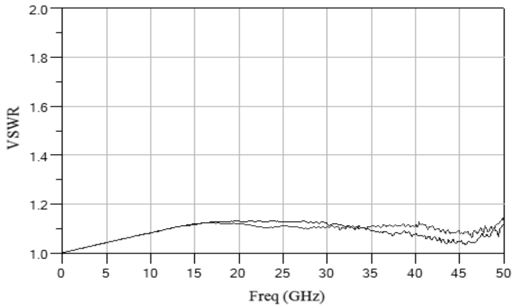
典型曲线：

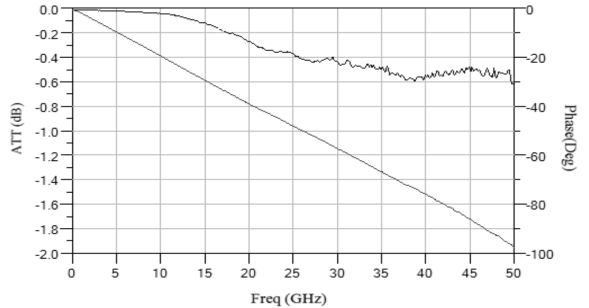
输入输出驻波比

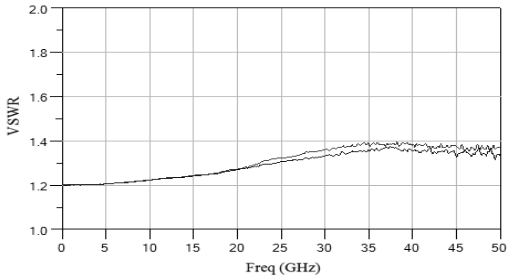
插损

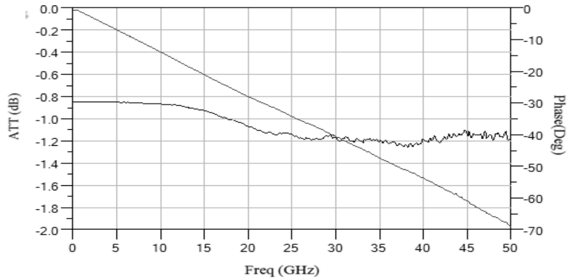


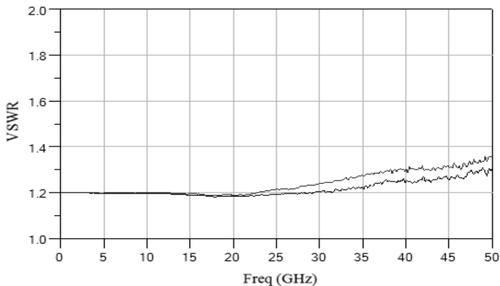


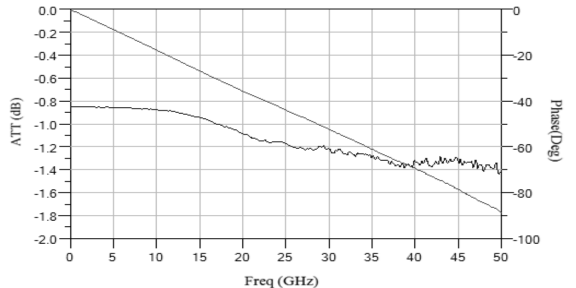


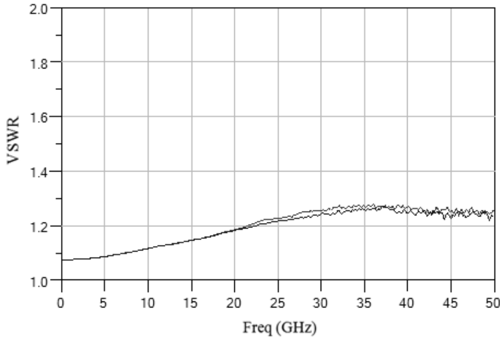


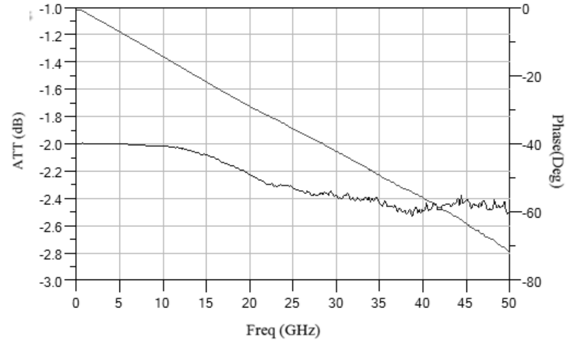


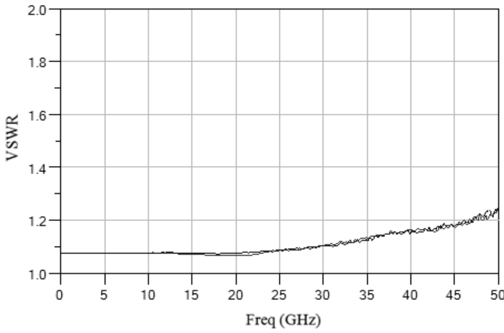


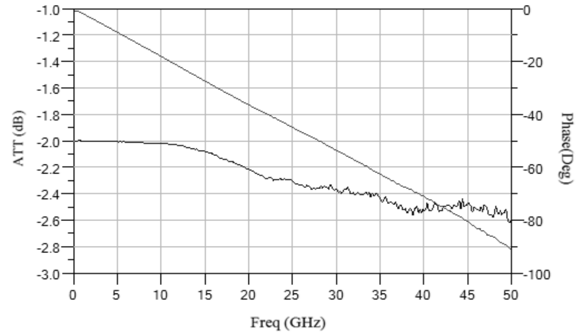


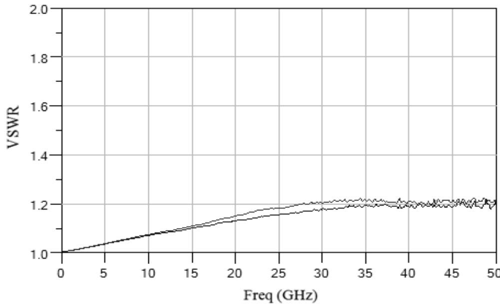


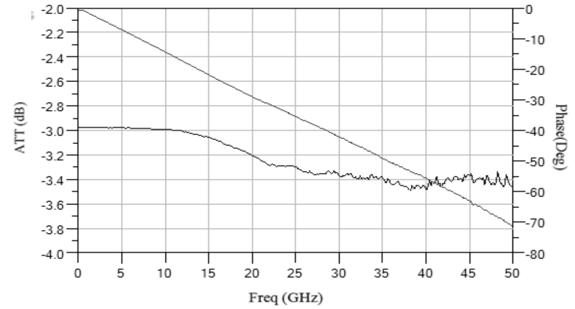


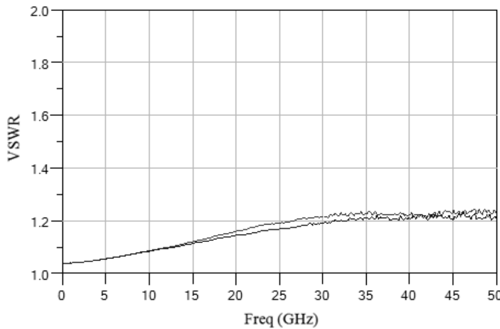


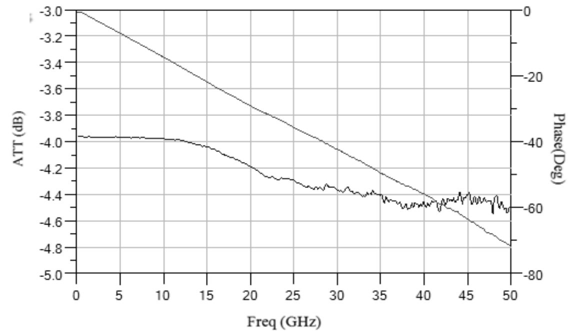












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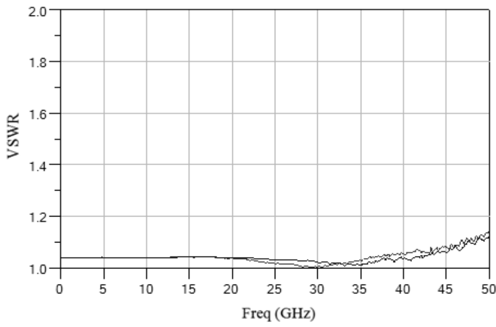

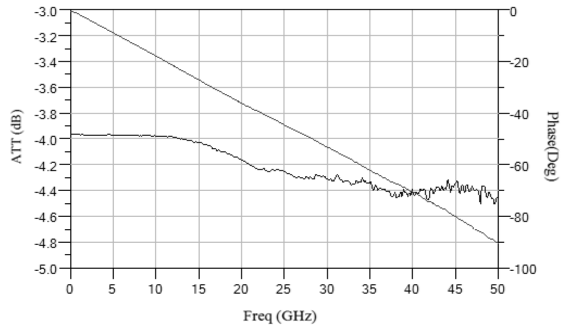

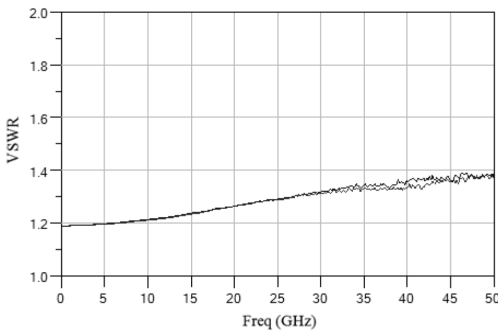

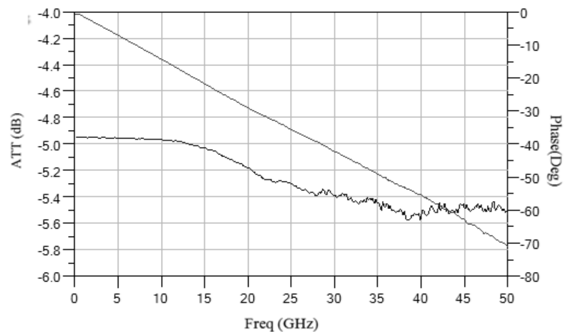

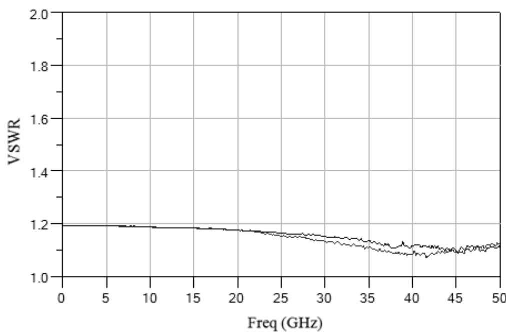

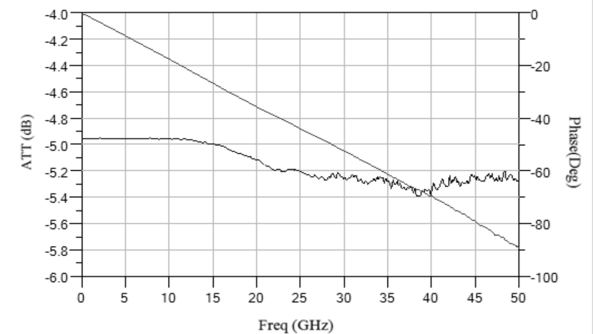

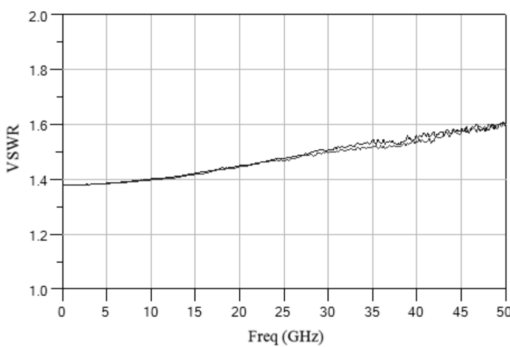

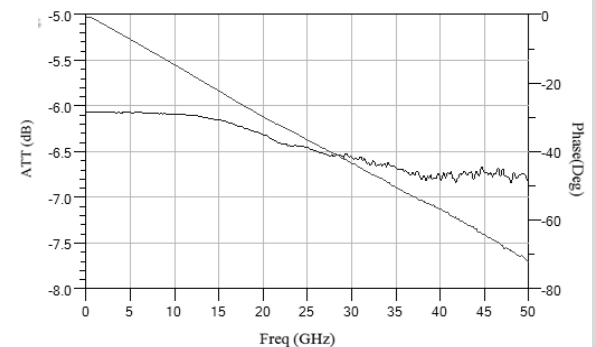

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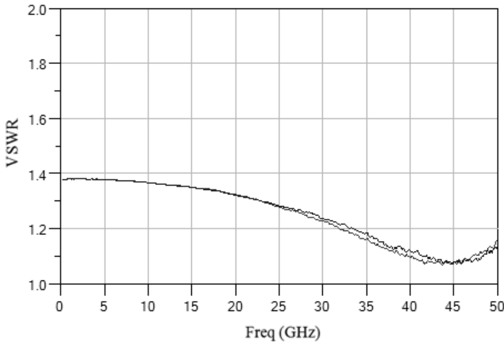

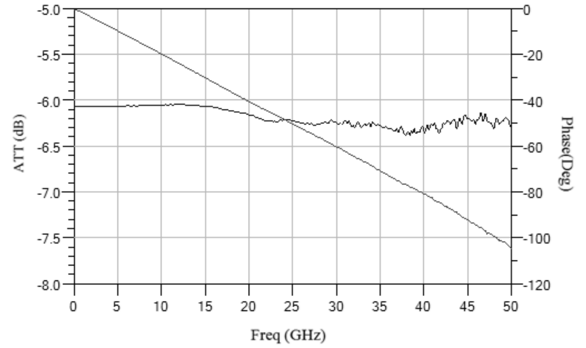

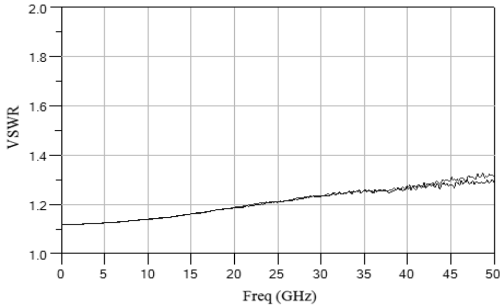

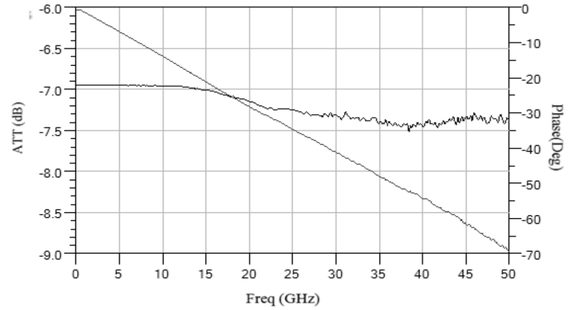

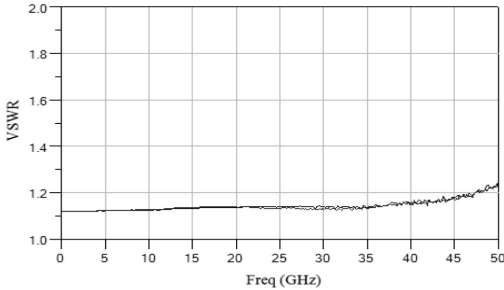

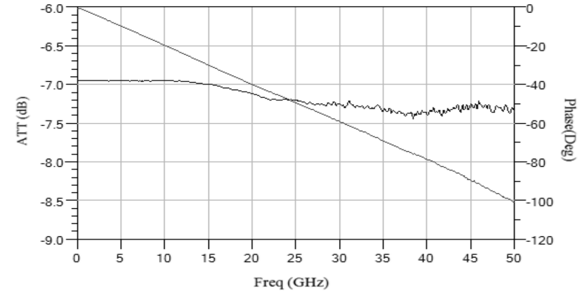

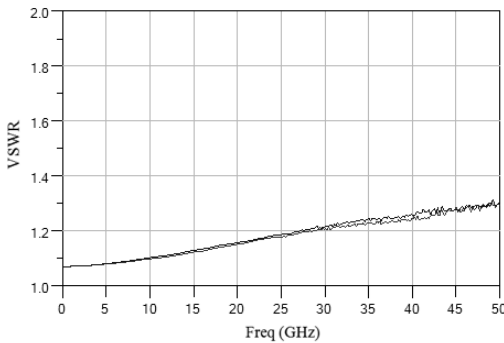

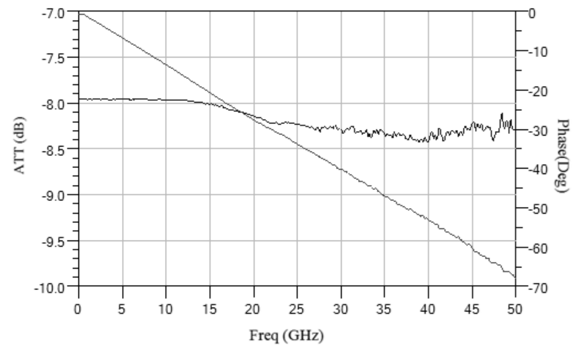

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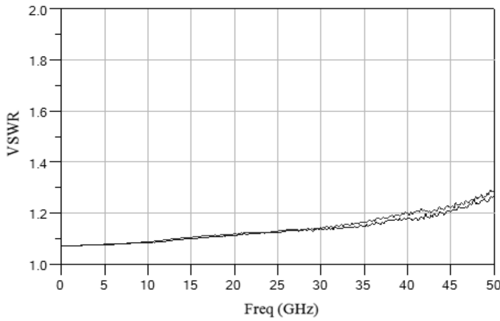
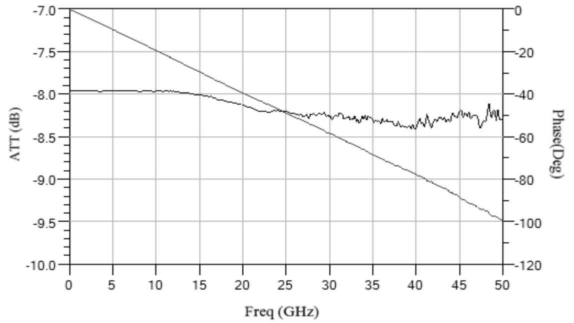
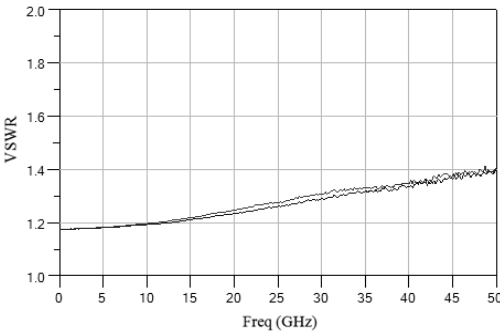
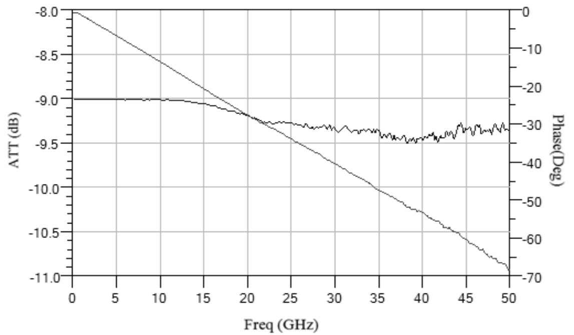
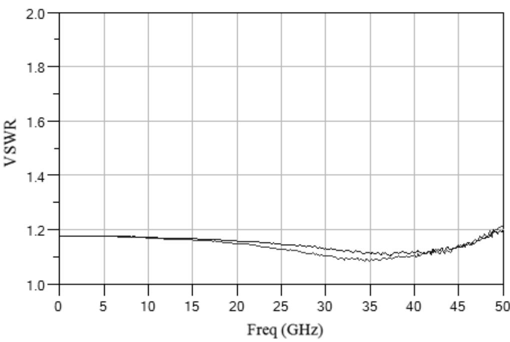
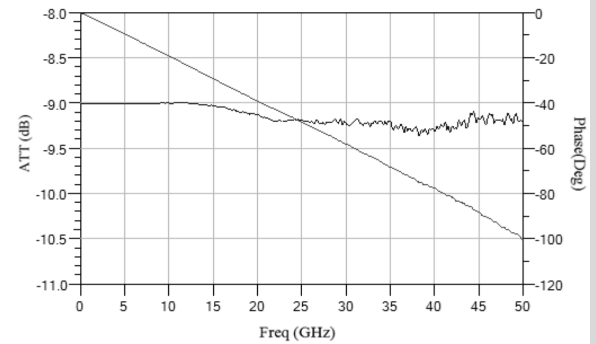

HW-ATT50-8(Bondwire)
VSWR
Freq (GHz)

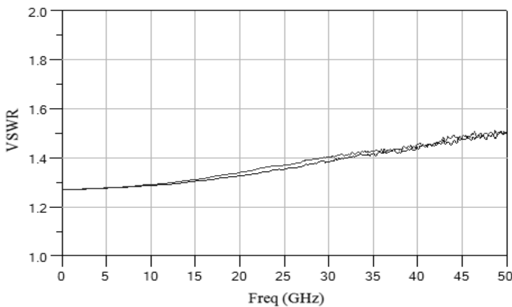

HW-ATT50-8(Bondwire)
ATT (dB)
Phase(Deg)
Freq (GHz)

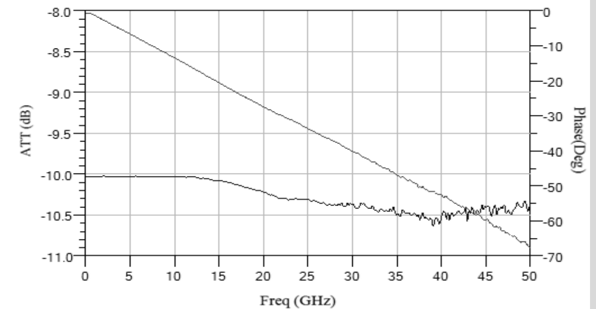

HW-ATT50-9(on-wafer)
VSWR
Freq (GHz)

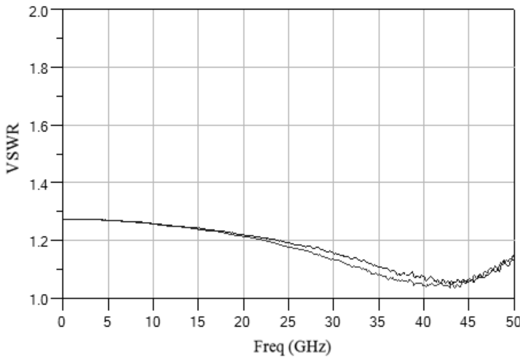

HW-ATT50-9(on-wafer)
ATT (dB)
Phase(Deg)
Freq (GHz)

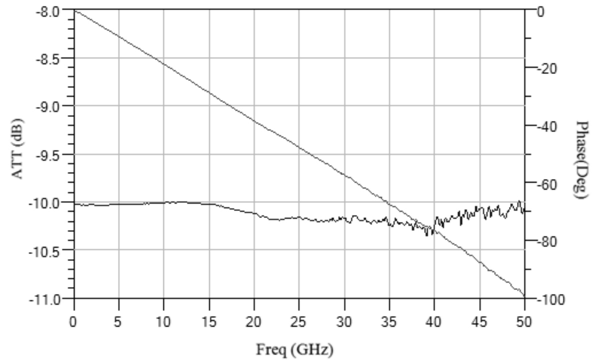

HW-ATT50-9(Bondwire)
VSWR
Freq (GHz)


HW-ATT50-9(Bondwire)
ATT (dB)
Phase(Deg)
Freq (GHz)

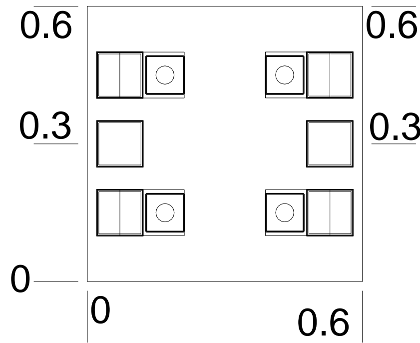

HW-ATT50-10(on-wafer)
VSWR
Freq (GHz)


HW-ATT50-10(on-wafer)
ATT (dB)
Phase(Deg)
Freq (GHz)

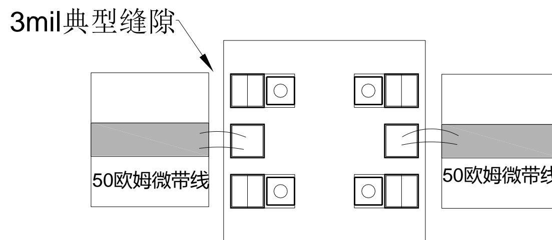




尺寸图：(单位 mm)



建议装配图：



使用说明：

存储：芯片必须放置于具有静电防护功能的容器中，并在氮气环境下保存。

清洁处理：裸芯片必须在净化环境中操作使用，禁止采用液态清洁剂对芯片进行清洁处理。

静电防护：请严格遵守 ESD 防护要求，避免器件静电损伤。

常规操作：拿取芯片请使用真空夹头或精密尖头镊子。操作过程中要避免工具或手指触碰到芯片表面。

装架操作：芯片安装可采用 AuSn 焊料共晶焊接或导电胶粘接工艺。安装面必须清洁平整。

键合操作：输入输出各用 2 根（建议直径 25um 金丝）键合线，键合线长度小于 250um 最优。建议采用尽可能小的超声波能量。键合时起始于芯片上的压点，终止于封装（或基板）。

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